

HFA1102

Ultra High-Speed Current Feedback Amplifier with Compensation Pin

July 1995

Features
Compensation Pin for Bandwidth Limiting
• Low Distortion (30MHz)56dBc
• -3dB Bandwidth 600MHz
• Very Fast Slew Rate 2000V/µs
• Fast Settling Time (0.1%)
Excellent Gain Flatness
- (100MHz)+0.05dB
- (50MHz)±0,02dB
- (30MHz) ±0.01dB
High Output Current 60mA
Overdrive Recovery<10ns

Applications

- · Video Switching and Routing
- · Pulse and Video Amplifiers
- · Wideband Amplifiers
- RF/IF Signal Processing
- Flash A/D Driver
- · Medical Imaging Systems

Description

The HFA1102 is a high speed wideband current feedback amplifier featuring a compensation pin for bandwidth limiting. Built with Harris' proprietary complementary bipolar UHF-1 process, it has excellent AC performance and low distortion.

Because the HFA1102 is already unity gain stable, the primary purpose for limiting the bandwidth is to reduce the total noise (broadband) of the circuit. The bandwidth of the HFA1102 may be limited by connecting a capacitor and series damping resistor from pin 8 to ground. Typical bandwidths for various values of compensation capacitors are shown in the Electrical Specifications section of this datasheet.

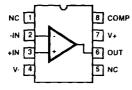
A variety of packages and temperature grades are available. See the ordering information below for details.

Ordering Information

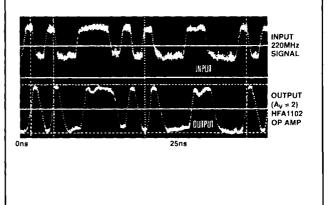
PART NUMBER	OPERATING TEMP RANGE	PRODUCT DESCRIPTION		
HFA1102IJ	-40°C to +85°C	8 Lead CerDIP		
HFA1102IP	-40°C to +85°C	8 Lead Plastic DIP		
HFA1102IB	-40°C to +85°C	8 Lead Plastic SOIC (N)		
HFA1102Y	-40°C to +85°C	Die		

Pinout

HFA1102 (PDIP, CERDIP, SOIC) TOP VIEW



The Op Amps with Fastest Edges



Specifications HFA1102

Operating Conditions Absolute Maximum Ratings Operating Temperature Range $\begin{array}{lll} & +85^{\circ}C \\ & +85^{\circ}C \end{array}$ Storage Temperature Range $\begin{array}{lll} & -40^{\circ}C \leq T_{A} \leq +85^{\circ}C \\ & -65^{\circ}C \leq T_{A} \leq +150^{\circ}C \end{array}$ DC Input VoltageV_{SUPPLY} Thermal Package Characteristics (°C/W) θ_{JA} θ_{JC} CerDIP Package 36 Junction Temperature (Ceramic and Die)....+175°C 116 Junction Temperature (Plastic Package) +150°C 130 N/A Lead Temperature (Soldering 10s)+300°C SOIC Package..... 170 N/A (SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ralings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Specifications $V_{SUPPLY} = \pm 5V, A_V = +1, R_F = 510\Omega, R_L = 100\Omega, C_{COMP} = 0pF.$ Unless Otherwise Specified

			HFA11021		UNITS
PARAMETER	TEMP	MIN	TYP	MAX	
INPUT CHARACTERISTICS					
Input Offset Voltage	+25°C	-	2	6	mV
	Full	-	-	10	mV
Input Offset Voltage Drift	Full	-	10		μV/°C
V_{IO} CMRR ($\Delta V_{CM} = \pm 2V$)	+25°C	40	46		dB
	Full	38			dB
V_{IO} PSRR ($\Delta V_S \approx \pm 1.25V$)	+25°C	45	50		dB
	Full	42		-	dB
Non-Inv. Input Bias Current (+IN = 0V)	+25°C	-	25	40	μА
	Full			65	μА
+I _{BIAS} Drift	Full		40	-	n A/° C
+I _{BIAS} CMS (ΛV _{CM} ≈ ±2V)	+25°C	-	20	40	μA/V
	Full	-	-	50	μA/V
Inv. Input Bias Current (-IN = 0V)	+25°C	,	12	50	μА
	Full	-		60	μА
-I _{BIAS} Drift	Full		40	-	nA/°C
-l _{BIAS} CMS (ΔV _{CM} = ±2V)	+25°C	-	1	7	μΑ∕∨
	Full	-		10	μA/V
-1_{BIAS} PSS ($\Delta V_S = \pm 1.25V$)	+25°C	-	6	15	μ Α /V
	Full	-	-	27	μA/V
Non-Inv. Input Resistance	+25°C	25	50		kΩ
Inv. Input Resistance	+25°C		16	30	73
Input Capacitance (either input)	+25°C	-	2		pF
Input Common Mode Range	Full	±2.5	±3.0		V
Input Noise Voltage (100kHz)	+25°C		4	-	nV/√Ha
+Input Noise Current (100kHz)	+25°C	-	18		pA∕√Ha
-Input Noise Current (100kHz)	+25°C		21		p A /√H:
TRANSFER CHARACTERISTICS $A_V = +1$, $R_F = 150\Omega$,	$R_{DAMP} = 120\Omega$, Unless O	therwise Spec	cified	<u> </u>	
Open Loop Transimpedance	+25°C	-	500		kΩ

Specifications HFA1102

PARAMETER Linear Phase Deviation (DC to 100MHz)			HFA1102I			T
		TEMP	MIN	TYP	MAX	UNITS
		+25°C	•	0.6	-	Degrees
Differential Gain (NTSC, $R_L = 75\Omega$)		+25°C	-	0.03	· · · · ·	%
Differential Phase (NTSC, $R_L = 75\Omega$)		+25°C	-	0.03		Degrees
Minimum Stable Gain		Full	1			V/V
Bandwidth Limiting Characteristics -3dB Bandwidth ($V_{OUT} = 0.2V_{P,P}$, $A_V = +1$)	C _{COMP} = 0pF	+25°C	-	600	-	MHz
	C _{COMP} = 1pF	+25°C	-	350	-	MHz
	C _{COMP} = 3pF	+25°C		190	-	MHz
	C _{COMP} = 7pF	+25°C		55		MHz
Gain Flatness (to 30MHz)						
	C _{COMP} = 0pF	+25°C	•	±0.01		dB
	C _{COMP} = 1pF	+25°C	-	±0.05	· ·	dB
	C _{COMP} = 3pF	+25°C	-	±0.10		dB
Gain Flatness (to 100MHz)		+25°C	-	±0.05		dB
Gain Flatness (to 50MHz)		+25°C	-	±0.02		d₿
OUTPUT CHARACTERISTICS A _V = +2, Unles	s Otherwise Specified	i	·			•
Output Voltage (A _V = -1)		+25°C	±3.0	±3.3] -	V
		Full	±2.5	±3.0	· ·	V
Output Current (R _L = 50Ω, A _V = -1)		+25°C	50	65		mA
		Full	40	60	-	mA
DC Closed Loop Output Impedance		+25°C	•	0.1	-	Ω
2nd Harmonic Distortion (30MHz, V _{OUT} = 2V _{P-P})		+25°C		-56	·	dBc
3rd Harmonic Distortion (30MHz, V _{OUT} = 2V _{P.P})		+25°C	-	-80	-	dBc
3rd Order Intercept (100MHz)		+25°C	•	30		dBm
1dB Compression (100MHz)		+25°C	-	20		dBm
TRANSIENT RESPONSE $A_V = +1$, $R_F = 150\Omega$	$R_{DAMP} = 120\Omega$, Unic	ss Otherwise	Specified			
Rise Time (V _{OUT} = 2.0V Step)		+25°C	-	600	-	ps
Overshoot (V _{OUT} = 2.0V Step)		+25°C	-	10	-	%
Siew Rate (A _V = +1, V _{OUT} = 5V _{P-P})		+25°C		1200	-	V/µs
Slew Rate (A _V = +2, V _{OUT} = 5V _{P-P})		+25°C	-	2000	-	V/µs
0.1% Settling (V _{OUT} = 2V to 0V)		+25°C		11	-	ns
0.2% Settling (V _{OUT} = 2V to 0V)		+25°C	-	7		ns
POWER SUPPLY CHARACTERISTICS				•		
Supply Voltage Range		Full	±4.5	-	±5.5	V
Supply Current		+25°C	-	21	26	mA
		Full		-	33	mA

Applications Information

Optimum Feedback Resistor (R_F)

All current feedback amplifiers require a feedback resistor, even for unity gain applications. The $R_{\rm F}$, in conjunction with the internal compensation capacitor, sets the dominant pole of the frequency response. Thus, the amplifier's bandwidth is inversely proportional to $R_{\rm F}$. The HFA1102 design is optimized for a 150 Ω $R_{\rm F}$, at a gain of +1. Decreasing $R_{\rm F}$ in a unity gain application decreases stability, leading to excessive peaking and overshoot. At higher gains the amplifier is more stable, so $R_{\rm F}$ can be decreased in a tradeoff of bandwidth vs. stability.

Bandwidth Limiting

The bandwidth of the HFA1102 may be limited by connecting a resistor (R_{DAMP}) and capacitor in series from pin 8 to GND. The series resister is required to damp the interaction between the package parasitics and C_{COMP} . Typical bandwidths for various values of compensation capacitor are shown in the specification tables. Because the HFA1102 is already unity gain stable, the main reason for limiting the bandwidth is to reduce the total noise (broadband) of the circuit. Additionally, compensating the HFA1102 allows the use of a lower value R_F for a given gain. The decreased bandwidth due to C_{COMP} offsets the bandwidth increase from the lower R_F , keeping the amplifier stable. Reducing R_F provides the double benefits of reduced DC errors $(-l_B \times R_F)$ and reduced total noise (ini \times R_F and 4KTR_F).

PC Board Layout

The frequency performance of this amplifier depends a great deal on the amount of care taken in designing the PC board. The use of low inductance components such as chip resistors and chip capacitors is strongly recommended, while a solid ground plane is a must!

Attention should be given to decoupling the power supplies. A large value $(10\mu F)$ tantalum in parallel with a small value chip $(0.1\mu F)$ capacitor works well in most cases.

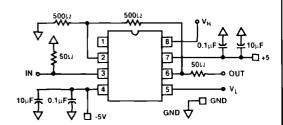
Terminated microstrip signal lines are recommended at the input and output of the device. Output capacitance, such as that resulting from an improperly terminated transmission line will degrade the frequency response of the amplifier and may cause oscillations. In most cases, the oscillation can be avoided by placing a resistor in series with the output.

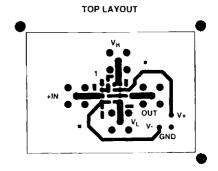
Care must also be taken to minimize the capacitance to ground seen by the amplifier's inverting input. The larger this capacitance, the worse the gain peaking, resulting in pulse overshoot and possible instability. To this end, it is recommended that the ground plane be removed under traces connected to pin 2, and connections to pin 2 should be kept as short as possible.

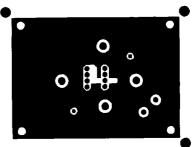
An example of a good high frequency layout is the Evaluation Board shown.

Evaluation Board

The HFA1102 may be evaluated using the HFA1130 Evaluation Board which is available from your local sales office. R_{DAMP} and C_{COMP} should be connected in series from the socket pin to the GND plane. The trace from pin 8 to the V_H connector should be cut near the socket to remove this parallel capacitance. The layout and schematic of the board are shown below:







Die Characteristics

DIE DIMENSIONS:

63 mils x 44 mils x 19 mils ±1mil 1600µm x 1130µm ±25.4µm

METALLIZATION:

Type: Metal 1: AlCu (2%)/TiWType: Metal 2: AlCu (2%)
Thickness: Metal 1: 8kÅ ±0.4kÅThickness: Metal 2: 16kÅ ±0.8kÅ

GLASSIVATION:

Type: Nitride

Thickness: 4kÅ ±0.5kÅ

DIE ATTACH:

Material: Epoxy - Plastic DIP and SOIC

WORST CASE CURRENT DENSITY:

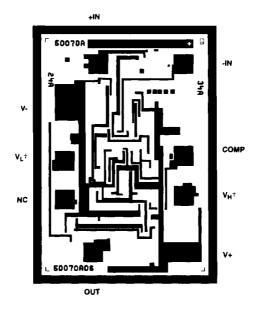
0.909 x 10⁵A/cm²

TRANSISTOR COUNT: 52

SUBSTRATE POTENTIAL (Powered Up): Floating (Recommend Connection to V-)

Metallization Mask Layout

HFA1102



† Output Clamping Function (V_H, V_L) is available to users of the HFA1102 in die form. Please refer to the HFA1130 data sheet for information regarding the operation and use of this function.